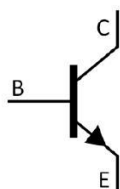


VRW056 ММ Ё QSQ Æ Ñ ы s ll 1 Silicon NPN transistor in a SOT-23 Plastic Package.

г б е ж з к н / о ф ч џ Ѡ ѡ Ѣ
Small reverse transfer capacitance, low noise figure.

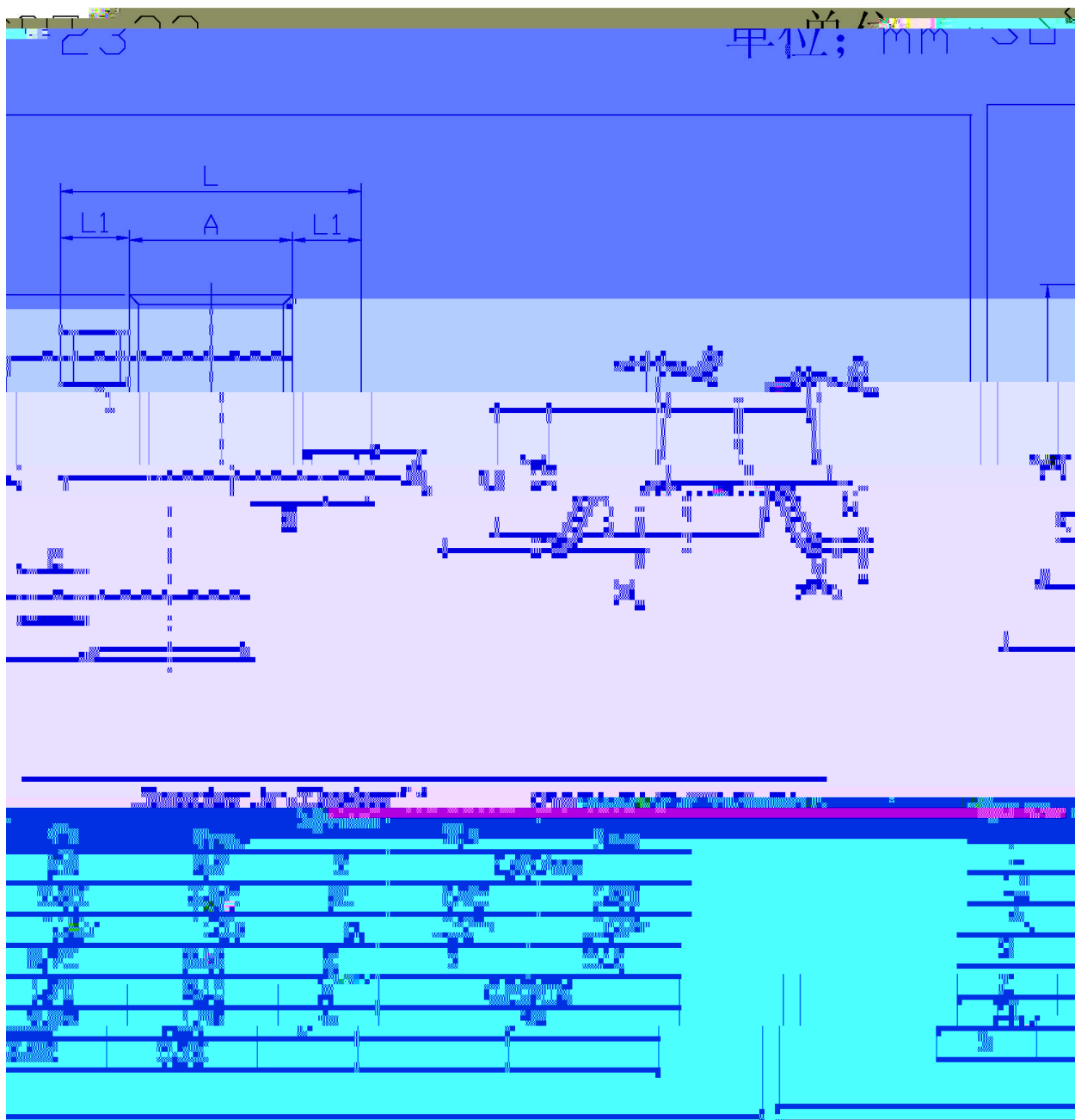
ƒ_{ce} ≈ 1 ѡ z
High frequency amplifier applications.



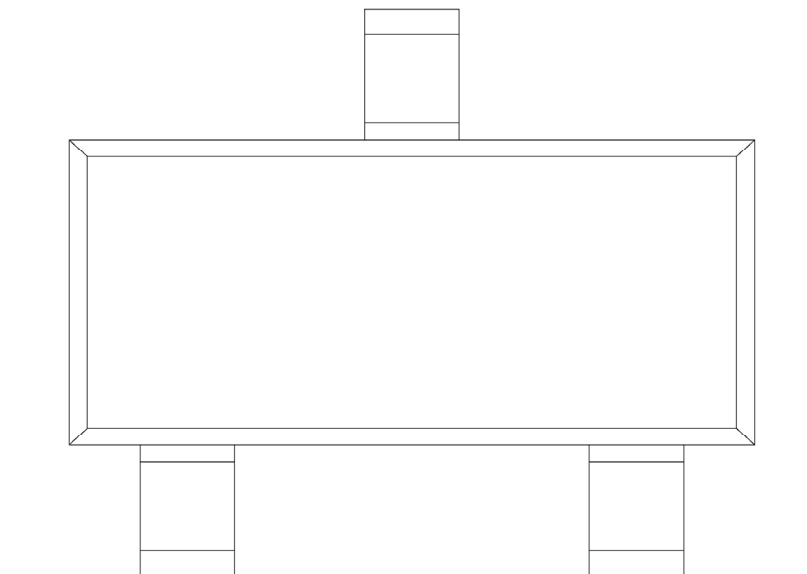
PIN1

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current	I_C	20	mA
Emitter Current	I_E		

/ Package Dimensions



/ Marking Instructions



б " X

K X № 3^И Пб

T X № 3^Н Пб

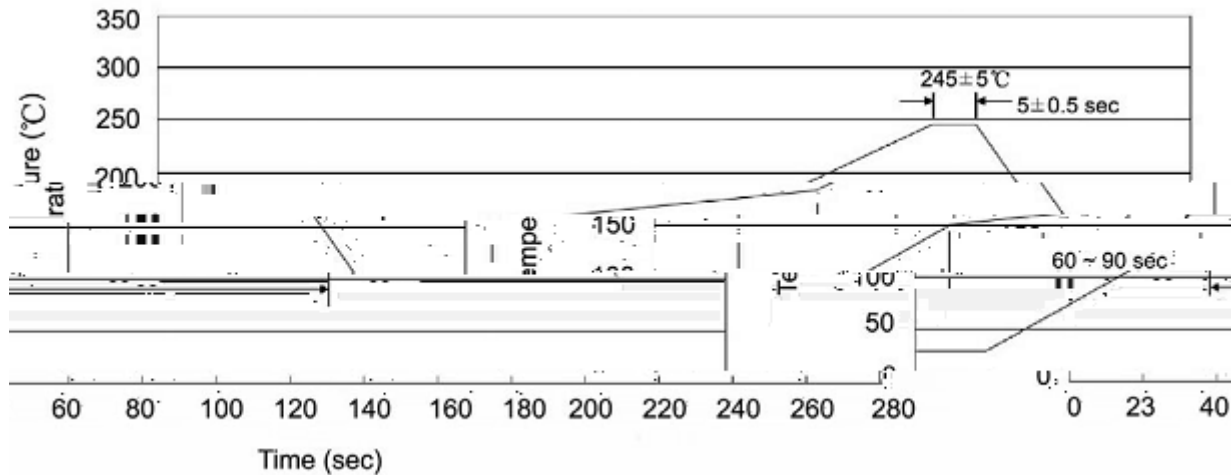
U X № h_{FE}⁶ К Пб

Note:

K X Company

7y

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



注意

1. 预加热: 25~150 °C, Time: 60~90sec;
2. 峰值温度: 245±5 °C, Duration: 5±0.5sec;
3. 冷却速度: 2~10 °C/sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 245±5 °C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Test Conditions

温度: 260±5 °C 时间: 10±1 sec. Temp.: 260±5 Time: 10±1 sec

/ Packaging SPEC.

包装形式 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7 × 8	180×120×180	390×385×205

/ Notices